

Field-Induced Resistive Switching in Metal-Oxide Interfaces

S. Tsui¹, A. Baikalov¹, J. Cmaidalka¹, Y. Y. Sun¹, Y. Q. Wang¹,
Y. Y. Xue¹, C. W. Chu^{1,2,3}, L. Chen⁴, and A. J. Jacobson⁴

¹*Department of Physics and Texas Center for Superconductivity and Advanced Materials,
University of Houston, 202 Houston Science Center, Houston, Texas 77204-5002*

²*Lawrence Berkeley National Laboratory, 1 Cyclotron Road, Berkeley, California 94720*

³*Hong Kong University of Science and Technology, Hong Kong and*

⁴*Department of Chemistry, University of Houston,
136 Fleming Building, Houston, Texas 77204-5003*

(Dated: November 2, 2018)

We investigate the polarity-dependent field-induced resistive switching phenomenon driven by electric pulses in perovskite oxides. Our data show that the switching is a common occurrence restricted to an interfacial layer between a deposited metal electrode and the oxide. We determine through impedance spectroscopy that the interfacial layer is no thicker than 10 nm and that the switch is accompanied by a small capacitance increase associated with charge accumulation. Based on interfacial $I - V$ characterization and measurement of the temperature dependence of the resistance, we propose that a field-created crystalline defect mechanism, which is controllable for devices, drives the switch.

Recent observation of room-temperature resistive switching driven by electric fields in various perovskite oxides has garnered attention due to the potential for nonvolatile memory applications. This field-induced resistive switch has been reported in several compounds.^{1,2,3,4,5,6} The switching observed shares several features: a moderate switch speed; an altered resistance inconsistent with the well-accepted bulk resistivity; and a sensitivity to surface treatments. Various models have been put forth, but inconsistencies remain. For instance, bulk charge ordering in $\text{Pr}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$ (PCMO) has been suggested, but this creates an apparent conflict with both the spatial symmetry and the reported bulk properties.¹ Although interface models have been proposed involving either lattice defects or carrier concentration,^{2,5,7} the exact nature of this interface remains vague. We therefore investigate the interface properties associated with the resistive switch and have observed: a) the switching is a common phenomenon to the metal-oxide interfacial layer; b) the interfacial transport properties are rather different from that of the bulk; c) the interfacial resistance is dominated by the carrier trapping with no indication of Schottky barriers; and d) the capacitance of the interfacial layer, on the order of 1000 nF/cm^2 , changes with switching, which is indicative of a change in the space-charge. These observations can be self-consistently understood using a carrier-trapping model and suggest that the field-induced switch is not restricted to a small class of materials. Therefore, the potential for controlling this phenomenon for device applications is considerable.

Ceramic samples synthesized by standard solid-state reactions were determined to be single-phase based on X-ray powder diffraction patterns taken on a Rigaku DMAX-IIIIB diffractometer. PCMO thin films were ac sputtered on LaAlO_3 substrates at 760°C in an $\text{Ar}:\text{O}_2 = 2 : 3$ mixed atmosphere at 140 mTorr. The films were found to be highly epitaxial. Pt leads were attached to

the ceramic samples using Ted Pella Leitsilber 200 Ag paint. The thin film samples received sputtered Ag electrodes to which Pt leads were also attached using Ag paint.

Ceramic LaCoO_3 , $\text{La}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$, $\text{Pr}_{0.7}\text{Ca}_{0.3}\text{MnO}_3$, $\text{SrFeO}_{2.7}$, $\text{RuSr}_2\text{GdCu}_2\text{O}_3$, and $\text{YBa}_2\text{Cu}_3\text{O}_7$ were tested. We adopted the multi-leads configuration developed by Baikalov *et al.*² to measure both the interfacial and bulk resistances of the samples (inset, Fig. 1). A DEI PVX-4150 pulse generator provided 150 V pulses of 200 ns width. A pair of electrodes (A and B in Fig. 1) at room temperature was exposed to twenty pulses spaced 3 s apart. As a typical example, data for LaCoO_3 (Fig. 1) revealed that the 4-leads bulk resistance $R_{\text{bulk}} \sim 100 \Omega$, which is consistent with previously published resistivity data,⁸ remained unaffected by the pulses within an experimental resolution of 0.01Ω . However, the 3-leads interfacial resistances, R_A and R_B measured through the reference electrode C , showed hysteretic and polarity-dependent switching between a low (on)- and a high (off)-resistance state. The interfacial resistances at both states are much higher than that expected from the bulk value. All other tested compounds behaved similarly when exposed to pulsing. The data therefore suggest that the switching is a common phenomenon, but associated only with an insulating interfacial layer. In view of the different spin configurations, valences, and band structures of the tested compounds, the field-induced polarity-dependent resistive switch is unlikely to be associated with a particular phase transition or carrier doping.

In order to better characterize this interface, impedance spectroscopy was performed on PCMO thin films using a Schlumberg er SI 1260 impedance analyzer with a Solartron 12603 attachment. Measurements spanned a frequency range of 0.1 Hz to 20 MHz. The single-layered PCMO strips received three parallel $0.2 \times 1.3 \text{ mm}^2$ Ag electrodes spaced 0.3 mm apart. The electrodes A and B experienced switching under the same

150 V, 200 ns wide pulses. Electrode C served as a reference electrode. Both the 2-leads impedances Z_{AB} and Z_{BC} were then measured. In general, the impedance can be modeled as three parallel RC circuits associated with the two interface regions and the bulk portion (inset, Fig. 2). Therefore, we expect the impedance spectrum to show three sections to account for our model, assuming that the corresponding time constants differ (Fig. 2).⁹

Indeed, Z_{AB} and Z_{BC} share a three-sectioned feature. The impedance spectra show two merged semi-circles that begin on the Z' axis. Below 1 kHz, the spectra terminate on the Z' axis at values that correspond to the total 2-leads dc resistance measured between the electrodes. Above 1 MHz, the spectrum again reaches the Z' axis at a left endpoint with a resistance in rough agreement with the bulk resistance measured in the 4-leads configuration. Therefore, the Z' segment between the origin and the endpoint is attributed to the bulk portion of the sample based on the negligible C_{AB} and C_{BC} estimated. It should be noted that the positions of the left endpoints are unaffected by the switching, which is a further indication of the bulk contribution. At the intermediate frequencies, both spectra are dominated by a large semicircle. In the case of Z_{AB} , it represents a parallel RC circuit of $700 \Omega/1.6 \text{ nF}$ and $1500 \Omega/2.2 \text{ nF}$ for the on- and off-states, respectively. We assign this feature to electrode B based on the measured dc interfacial resistances. Similar results were obtained for Z_{BC} with some difference in the R_B and C_B deduced. We attribute the differences to inhomogeneity along the width of electrode B . An additional small segment appearing as a merged semicircle between these two major features is attributed to electrodes A and C , respectively. The interpretation is supported by the fact that the R_C and C_C deduced are not altered by switching, and the three-leads R_A changes only slightly with switching.

We expanded upon the spectroscopy data with a capacitance measurement across a multilayered Ag/PCMO/Pt sandwich similar to the configuration used by Liu *et al.*¹ In order to properly measure the capacitance of the interface, bypass current through the Pt bottom layer had to be prevented. This was achieved by making the Pt layer ultrathin with poor in-layer conductance, creating an overall resistance $\sim 10 \text{ k}\Omega$ between a switched electrode and a reference electrode. As a result, we were able to directly measure the interfacial 1.5 nF capacitance, a value consistent with the above spectrum analysis, using the 3-leads configuration with a HP 4285A LCR meter.

Knowing the capacitance C , the thickness of the interfacial layer, $d = \epsilon_0 \epsilon S/C$, can be estimated, where ϵ_0 , ϵ , and S are the vacuum permittivity, the dielectric constant, and the electrode area, respectively. With $\epsilon_0 = 8.85 \times 10^{-14} \text{ F/cm}$, $C \sim 2 \times 10^{-9} \text{ F}$, and $S = 0.02 \times 0.13 \text{ cm}^2$, a d is obtained to be 1 and 10 nm with $\epsilon = 1$ and 10, respectively.¹⁰ Thus, the switching layer seems to involve no more than 30 unit cells in the thickness.

To further characterize the switching mechanism, we

investigated the temperature dependence of the resistance and the $I - V$ characteristics of the interface. The temperature dependences of the interfacial resistances of the PCMO ceramic at both on- and off-states were found to be identical (dashed lines, inset, Fig. 3), demonstrating that the hopping barrier, hence the mobility, is the same in both states. However, the temperature dependence of the bulk (solid line, inset, Fig. 3) differs visibly from that of the interfaces, suggesting that the interfacial layers are significantly altered.

Carrier transport in insulators and semiconductors has been extensively studied. The dominant factor will either be space-charge limited currents (SCLC), in which the carrier injection from the electrode is limited by the electric field of the accumulated space charges, or the carrier creation through thermionic emission limited conduction (TELC), electrothermal Poole-Frenkel emission, or Fowler-Nordheim quantum tunneling. These modes can be distinguished via the isothermal $I - V$ correlation: linear $I \propto V$ for TELC; exponential $\ln I \propto V$ for Poole-Frenkel or Fowler-Nordheim emission; and $I \propto V^2$ for SCLC.¹¹ Asymmetry in the $I - V$ polarities would suggest additional Schottky barriers.

The $I - V$ characteristics obtained for a Ag/ceramic PCMO interfacial layer (Fig. 3) show linear behavior up to approximately 0.1 V, suggesting that TELC is the dominant mechanism at the lower voltage regime where carrier injection plays a minor role. Beyond that, the behavior evolves into SCLC, as determined by the fit $I \propto V^{2.3}$ above 0.5 V. In this upper regime, carrier injection from the electrodes plays a dominant role. It is interesting to note that the resistance ratio in both regions is roughly voltage-independent. The data also show no appreciable asymmetry with the $I - V$ polarity within $\pm 1 \text{ V}$, so the role of Schottky barriers appears to be minor, if it exists at all.

Analysis of the SCLC regime can be carried out using widely accepted models. Rose¹² and Lampert¹³ obtained

$$I = (\epsilon \mu_0 N_c e^{-E/kT}) V^2 / (N_t t^3), \quad (1)$$

where ϵ is the dielectric constant, μ_0 is the free carrier drift mobility, N_c is the effective density of states in the valence band, E is the effective trapping potential, N_t is the number of shallow traps, T is temperature, V is applied voltage, and t is the distance between electrodes. In particular, the doping level (or the carrier-creation rate) will not affect transport in SCLC, in which the dominant carriers are injected from the electrodes. The remaining factors will be the mobility and the fraction of free charge θ given by

$$\theta = (N_c/N_t) e^{-E/kT}. \quad (2)$$

Both parameters will alter the resistance. However, significant changes in E or μ_0 contend with the identical temperature dependences of the on- and off-states (inset,

Fig. 3). On the other hand, the pulse field of 10^7 V/cm is close to the decomposition threshold and can conceivably create dense crystalline defects through electromigration. We consequently propose that a pulse-driven reversible change of the trap density, roughly a 5–100 \times variation, is responsible for the switching. The variation of C_B with switching (Fig. 2) suggests a change in the space-charge distribution and supports the model. It should be noted that the same carrier trapping will increase the resistance in the TELC regime by the same factor, in agreement with our data.

In conclusion, we demonstrate that field-induced resistive switching is a common recurring phenomenon restricted to an interfacial layer between a metal and a perovskite oxide. We also characterize the interfacial layer responsible for the switching as an insulating region no thicker than 10 nm. Further characterization through $I - V$ measurements and the temperature dependence of resistance enables us to propose a conduction mech-

anism dominated by pulse-generated crystalline defects. The results obtained in the present study suggest that the switching is not compound-specific and can be optimized for device applications by modifying the interface.

Acknowledgments

The work in Houston is supported in part by NSF Grant No. DMR-9804325, the T. L. L. Temple Foundation, the John J. and Rebecca Moores Endowment, the Robert A. Welch Foundation, and the State of Texas through the Texas Center for Superconductivity at the University of Houston; and at Lawrence Berkeley Laboratory by the Director, Office of Science, Office of Basic Energy Sciences, Division of Materials Sciences and Engineering of the U.S. Department of Energy under Contract No. DE-AC03-76SF00098.

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FIG. 1: Simultaneous switching of two electrodes on ceramic LaCoO_3 using twenty 150 V pulses of 200 ns width and 3 s apart. After pulsing, ten data points were measured. This was followed by another session of pulsing, after which another ten points were measured, as demarcated by the sequential count. The bold plot at the bottom shows the 4-leads bulk resistance. The open triangle plot shows the 3-leads interfacial resistance R_A , and the open circle plot shows R_B . This data is typical of the perovskite oxides we tested.

FIG. 2: Impedance spectra for a PCMO thin-film strip. Squares represent measurements over Z_{BC} whereas circles represent Z_{AB} . Open and solid symbols represent the on- and off-states, respectively.

FIG. 3: $I - V$ data show TELC behavior in the lower voltage regime and SCLC behavior in the higher regime with $I \propto V^{2.3}$. The inset shows a visible difference in the temperature dependence between the interfacial and bulk resistances.

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